

Tomas Bryllert

List of Publications by Year in descending order

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1075
citing authors

#	ARTICLE	IF	CITATIONS
1	220-GHz imaging radar with 1 Hz frame rate using an array of homodyne transceivers. , 2018, , .	2	
2	A 110-170 GHz transceiver in 130 nm SiGe BiCMOS technology for FMCW applications. , 2018, , .	0	
3	Optomechanical System Design for Dual-Mode Stand-Off Submillimeter Wavelength Imagers. IEEE Transactions on Terahertz Science and Technology, 2017, 7, 393-403.	3.1	11
4	220GHz wideband 3D imaging radar for concealed object detection technology development and phenomenology studies. Proceedings of SPIE, 2016, , .	0.8	4
5	A 474 GHz HBV Frequency Quintupler Integrated on a 20 μ m Thick Silicon Substrate. IEEE Transactions on Terahertz Science and Technology, 2014, , 1-7.	3.1	6
6	Single-Flange 2-Port TRL Calibration for Accurate THz <math formulatype="inline"><math Notation="TeX">\$\mu\text{m}^2\$</math></math formulatype="inline"><math Notation="TeX">S</math></math formulatype="inline">-Parameter Measurements of Waveguide Integrated Circuits. IEEE Transactions on Terahertz Science and Technology, 2014, 4, 582-587.	3.1	5
7	Sub-millimeter wave diode transceivers. , 2014, , .	1	
8	Molecular Spectroscopy With a Compact 557-GHz Heterodyne Receiver. IEEE Transactions on Terahertz Science and Technology, 2014, 4, 469-478.	3.1	18
9	Monolithically-Integrated Millimetre-Wave Wavelet Transmitter With On-Chip Antenna. IEEE Microwave and Wireless Components Letters, 2014, 24, 625-627.	3.2	51
10	Integrated 200â€“240-GHz FMCW Radar Transceiver Module. IEEE Transactions on Microwave Theory and Techniques, 2013, 61, 3808-3815.	4.6	73
11	Silicon Integrated InGaAs/InAlAs/AlAs HBV Frequency Tripler. IEEE Electron Device Letters, 2013, 34, 843-845.	3.9	10
12	Slot-Coupled Millimeter-Wave Dielectric Resonator Antenna for High-Efficiency Monolithic Integration. IEEE Transactions on Antennas and Propagation, 2013, 61, 1599-1607.	5.1	26
13	Thermal analysis of III-V HBV diode structures on InP, GaAs, silicon and diamond substrates. , 2013, , .	1	
14	Analytical Extraction of a Schottky Diode Model From Broadband S-Parameters. IEEE Transactions on Microwave Theory and Techniques, 2013, 61, 1870-1878.	4.6	71
15	Single flange 2-port design for THz integrated circuit S-parameter characterization. , 2013, , .	0	
16	Monolithic HBV-Based 282-GHz Tripler With 31-mW Output Power. IEEE Electron Device Letters, 2012, 33, 800-802.	3.9	17
17	A 175 GHz HBV Frequency Quintupler With 60 mW Output Power. IEEE Microwave and Wireless Components Letters, 2012, 22, 76-78.	3.2	13
18	Submillimeter Wave <math formulatype="inline"><math Notation="TeX">S</math></math formulatype="inline">-Parameter Characterization of Integrated Membrane Circuits. IEEE Microwave and Wireless Components Letters, 2011, 21, 110-112.	3.2	8

#	ARTICLE	IF	CITATIONS
19	VNA-calibration and S-parameter characterization of submillimeter wave integrated membrane circuits., 2010, , .	4	
20	A broadband heterostructure barrier varactor tripler source. , 2010, , .	1	
21	A monolithic 280 GHz HBV frequency tripler. , 2010, , .	0	
22	Time-Delay Multiplexing of Two Beams in a Terahertz Imaging Radar. IEEE Transactions on Microwave Theory and Techniques, 2010, 58, 1999-2007.	4.6	19
23	Confocal Ellipsoidal Reflector System for a Mechanically Scanned Active Terahertz Imager. IEEE Transactions on Antennas and Propagation, 2010, 58, 1834-1841.	5.1	89
24	High power w-band monolithically integrated tripler. , 2009, , .	7	
25	A 600 GHz imaging radar for concealed objects detection. , 2009, , .	19	
26	Penetrating 3-D Imaging at 4- and 25-m Range Using a Submillimeter-Wave Radar. IEEE Transactions on Microwave Theory and Techniques, 2008, 56, 2771-2778.	4.6	294
27	A 0.2-W Heterostructure Barrier Varactor Frequency Tripler at 113 GHz. IEEE Electron Device Letters, 2007, 28, 340-342.	3.9	27
28	Vertical wrap-gated nanowire transistors. Nanotechnology, 2006, 17, S227-S230.	2.6	159